10-EY07PMA050I7-L184A28T
datasheet

***flow*PIM E2** **650 V / 50 A**

Topology features

- Open Emitter configuration
- Temperature sensor
- Converter+Brake+Inverter

Component features

- Easy paralleling
- Low collector emitter saturation voltage
- Low turn-off losses
- Positive temperature coefficient

Housing features

- Base isolation: Al_2O_3
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

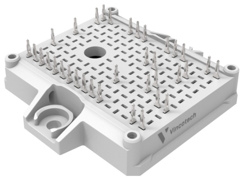
Target applications

- Industrial Drives

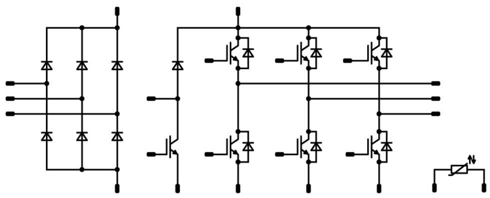
Types

- 10-EY07PMA050I7-L184A28T

flow E2 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Inverter Switch					
Collector-emitter voltage	V_{CES}			650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	56	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		150	A
Turn off safe operating area		T_j = 150°C, V_{CE} = 1200 V		150	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	81	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 400 V	T_j = 150 °C	3	µs
Maximum junction temperature	T_{jmax}			175	°C
Inverter Diode					
Peak repetitive reverse voltage	V_{RRM}			650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	42	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		150	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	61	W
Maximum junction temperature	T_{jmax}			175	°C
Brake Switch					
Collector-emitter voltage	V_{CES}			650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$	T_s = 80 °C	56	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		150	A
Turn off safe operating area		T_j = 150°C, V_{CE} = 1200 V		150	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	81	W
Gate-emitter voltage	V_{GES}			±20	V
Short circuit ratings	t_{SC}	V_{GE} = 15 V, V_{CC} = 400 V	T_j = 150 °C	3	µs
Maximum junction temperature	T_{jmax}			175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions		Value	Unit
Brake Diode					
Peak repetitive reverse voltage	V_{RRM}			650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	25	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		60	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	41	W
Maximum junction temperature	T_{jmax}			175	°C
Rectifier Diode					
Peak repetitive reverse voltage	V_{RRM}			1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$	T_s = 80 °C	58	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	T_j = 150 °C	400	A
Surge current capability	I^2t			800	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	68	W
Maximum junction temperature	T_{jmax}			150	°C
Module Properties					
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{isol}	DC Test Voltage*	t_p = 2 s	6000	V
Creepage distance				>12,7	mm
Clearance				8,83	mm
Comparative Tracking Index	CTI			≥ 600	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_{F} [V]	I_{C} [A] I_{D} [A] I_{F} [A]	T_{j} [°C]	Min	Typ	Max	Unit
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0005	25	4,35	5	5,65	V
Collector-emitter saturation voltage	V_{CEsat}		15		50	25 125 150		1,3 1,36 1,38	1,65(1)	V
Collector-emitter cut-off current	I_{CES}		0	650		25			20	µA
Gate-emitter leakage current	I_{GES}		20	0		25			100	nA
Internal gate resistance	r_{g}							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		3050		pF
Output capacitance	C_{oes}							92		pF
Reverse transfer capacitance	C_{res}							31		pF
Gate charge	Q_{g}	V_{CC} = 520 V	15		50	25		290		nC
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,17		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	±15	300	50	25 125 150		60,79 64,41 65,69		ns
Rise time	t_{r}					25 125 150		27,12 29,04 29,23		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		120,07 149,77 155,45		ns
Fall time	t_{f}					25 125 150		29,98 54,2 61,97		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,889 µC Q_{rFWD}=2,03 µC Q_{rFWD}=2,38 µC				25 125 150		0,781 1,06 1,15		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,669 1,02 1,13		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				50	25 125 150		1,68 1,58 1,56	2(1)	V
Reverse leakage current	I_R	V_r = 650 V				25			20	μA
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,57		K/W
Dynamic										
Peak recovery current	I_{RM}	di/dt=1324 A/μs di/dt=1330 A/μs di/dt=1286 A/μs	±15	300	50	25 125 150		17,13 26,09 28,27		A
Reverse recovery time	t_{rr}					25 125 150		88,19 131,34 144,52		ns
Recovered charge	Q_r					25 125 150		0,889 2,03 2,38		μC
Reverse recovered energy	E_{rec}					25 125 150		0,139 0,347 0,42		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		696,24 388,79 321,58		A/μs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Brake Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0005	25	4,35	5	5,65	V
Collector-emitter saturation voltage	V_{CEsat}		15		50	25 125 150		1,3 1,36 1,38	1,65(1)	V
Collector-emitter cut-off current	I_{CES}		0	650		25			20	µA
Gate-emitter leakage current	I_{GES}		20	0		25			100	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}	f = 1 Mhz	0	25		25		3050		pF
Output capacitance	C_{oes}							92		pF
Reverse transfer capacitance	C_{res}							31		pF
Gate charge	Q_g	V_{CC} = 520 V	15		50	25		290		nC
Thermal										
Thermal resistance junction to sink(2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,17		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	0/15	400	50	25 125 150		19,51 21,44 21,76		ns
Rise time	t_r					25 125 150		32,4 33,26 33,24		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		200,98 236,87 245,87		ns
Fall time	t_f					25 125 150		18,98 40,64 48,27		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,617 µC Q_{rFWD}=1,37 µC Q_{rFWD}=1,59 µC				25 125 150		1,15 1,45 1,52		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,843 1,29 1,42		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Diode										
Static										
Forward voltage	V_F				20	25 125 150		1,71 1,6 1,55	2[(1)]	V
Reverse leakage current	I_R	V_r = 650 V				25			20	µA
Thermal										
Thermal resistance junction to sink[(2)]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,32		K/W
Dynamic										
Peak recovery current	I_{RM}	di/dt=994 A/µs di/dt=1073 A/µs di/dt=1113 A/µs	0/15	400	50	25 125 150		10,77 15,83 16,89		A
Reverse recovery time	t_{rr}					25 125 150		95,93 139,24 155,48		ns
Recovered charge	Q_r					25 125 150		0,617 1,37 1,59		µC
Reverse recovered energy	E_{rec}					25 125 150		0,139 0,345 0,404		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		386,89 203,31 166,65		A/µs

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Rectifier Diode										
Static										
Forward voltage	V_F				5	25 125 150		0,875 0,764 0,748	1,1[1]	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 2000	µA
Thermal										
Thermal resistance junction to sink[2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,03		K/W
Thermistor										
Static										
Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	R_{100} = 499 Ω				100	3,2		3,3	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,3		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3380		K
Vincotech Thermistor Reference									V	

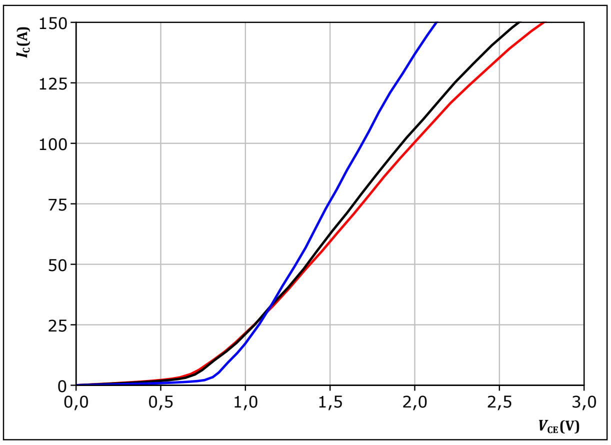
(1) Value at chip level
(2) Only valid with pre-applied Vincotech thermal interface material.

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

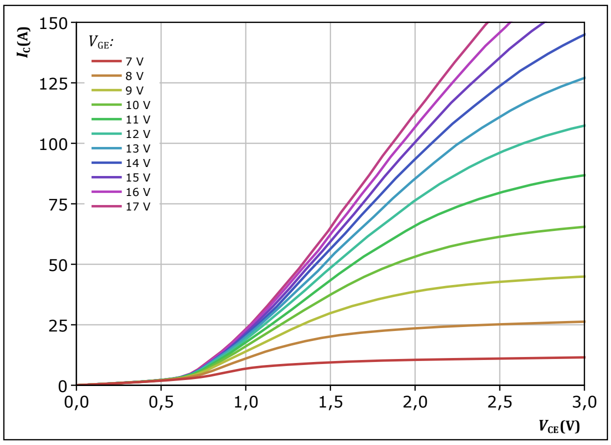


t_p =	250	µs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 2. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



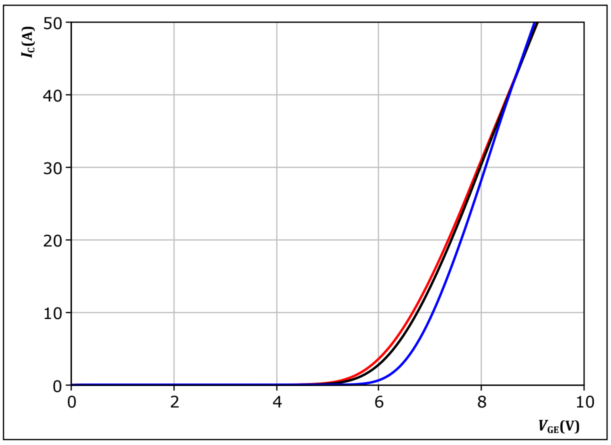
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 3. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})

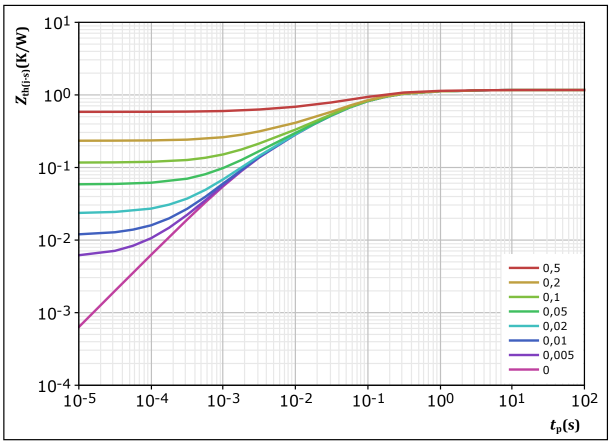


t_p =	250	µs		25 °C
V_{CE} =	9	V	T_j:	125 °C
				150 °C

figure 4. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j-s)}$ =	1,168	K/W

IGBT thermal model values

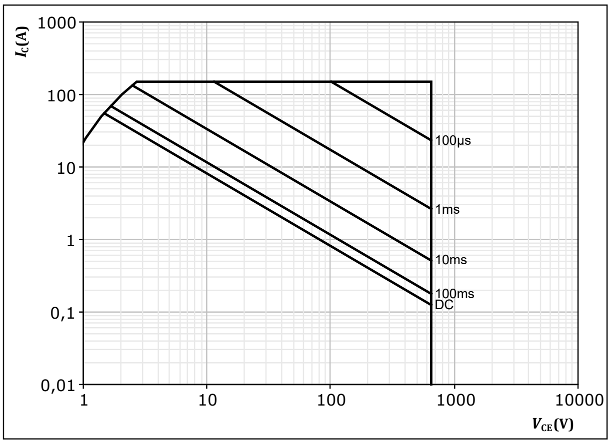
R (K/W)	τ (s)
6,39E-02	2,27E+00
2,30E-01	2,73E-01
5,97E-01	6,47E-02
2,01E-01	1,18E-02
7,68E-02	2,11E-03

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

I_C = f(V_{CE})

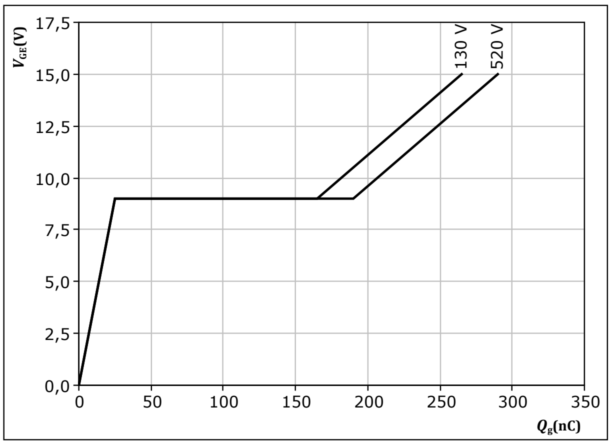


D = single pulse
T_s = 80 °C
V_{GE} = 15 V
T_j = T_{jmax}

figure 6. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



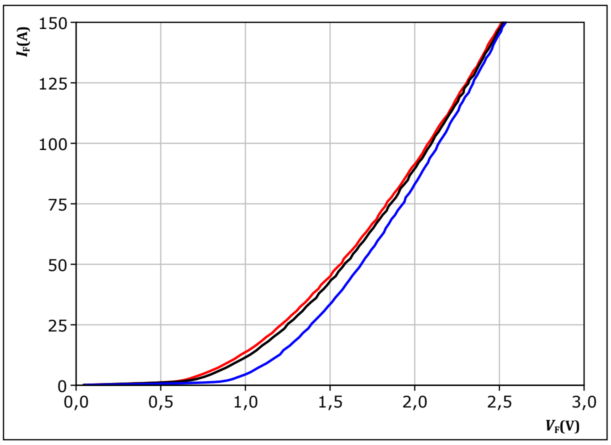
I_C = 50 A
T_j = 25 °C

Inverter Diode Characteristics

figure 7. **FWD**

Typical forward characteristics

I_F = f(V_F)



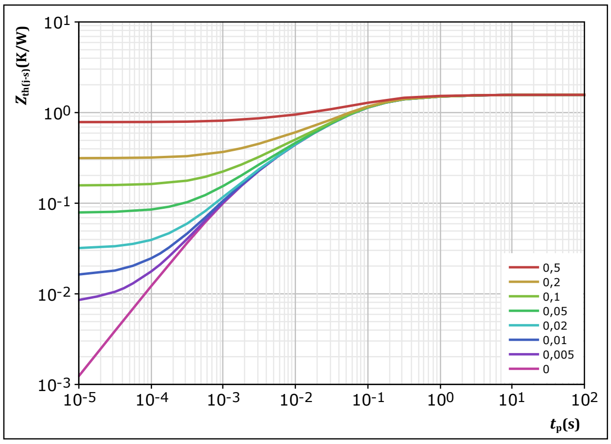
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 8. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D = t_p / T

$R_{th(j-s)}$ = 1,57 K/W

FWD thermal model values

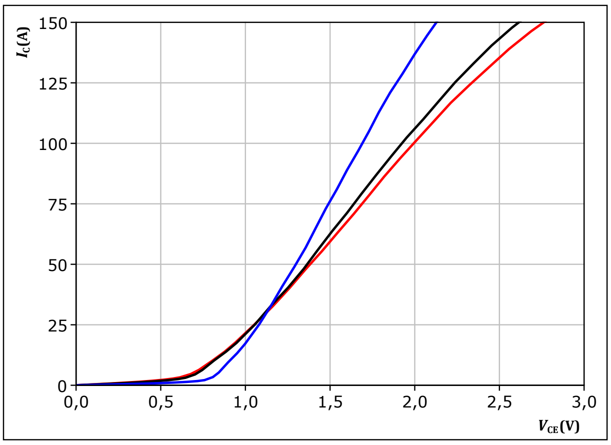
R (K/W)	τ (s)
9,68E-02	2,10E+00
2,69E-01	2,63E-01
7,78E-01	6,23E-02
3,22E-01	9,06E-03
1,04E-01	1,39E-03

Brake Switch Characteristics

figure 9. **IGBT**

Typical output characteristics

I_C = f(V_{CE})

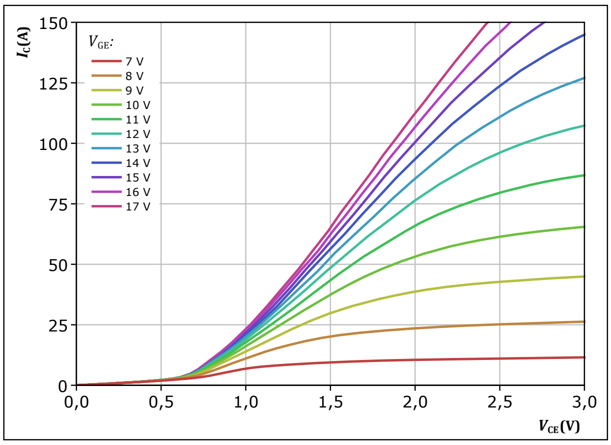


t_p =	250	µs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 10. **IGBT**

Typical output characteristics

I_C = f(V_{CE})



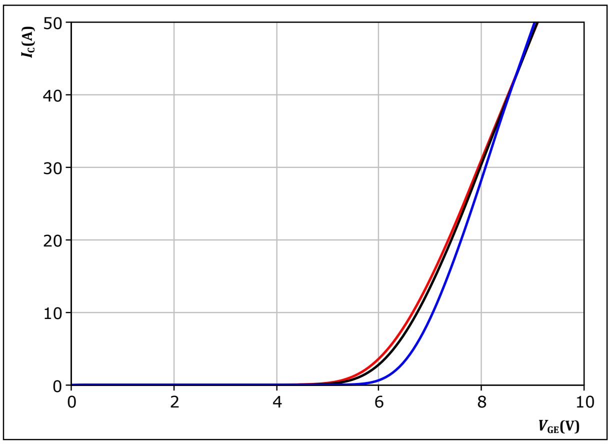
t_p =	250	µs
T_j =	150	°C

V_{GE} from 7 V to 17 V in steps of 1 V

figure 11. **IGBT**

Typical transfer characteristics

I_C = f(V_{GE})

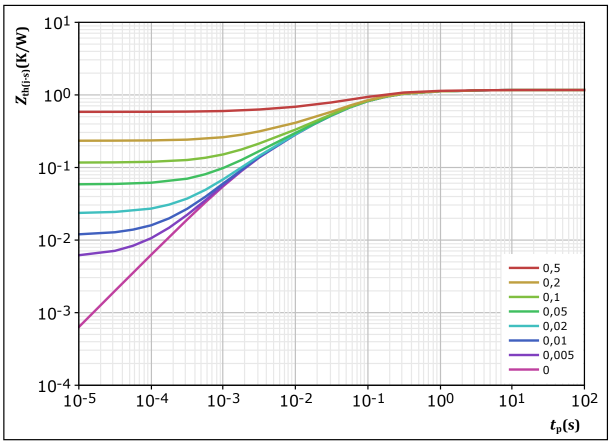


t_p =	250	µs		25 °C
V_{CE} =	9	V	T_j:	125 °C
				150 °C

figure 12. **IGBT**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)}$ = f(t_p)



D =	t_p / T	
$R_{th(j-s)}$ =	1,168	K/W

IGBT thermal model values

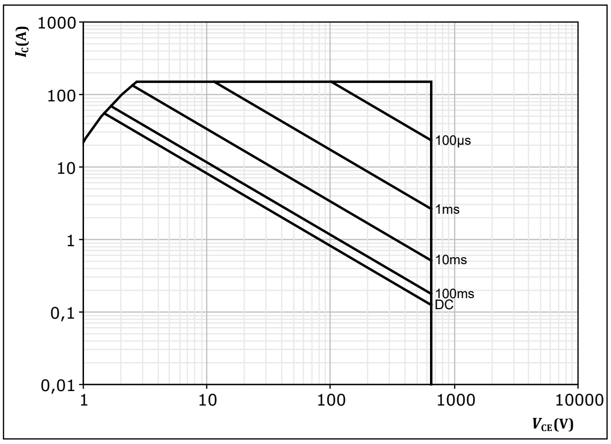
R (K/W)	τ (s)
6,39E-02	2,27E+00
2,30E-01	2,73E-01
5,97E-01	6,47E-02
2,01E-01	1,18E-02
7,68E-02	2,11E-03

Brake Switch Characteristics

figure 13. **IGBT**

Safe operating area

I_C = f(V_{CE})

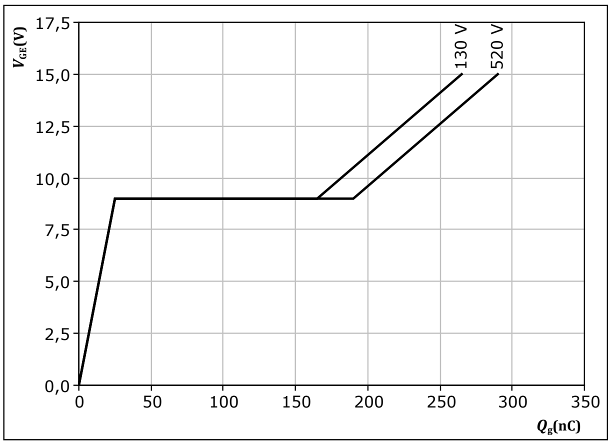


D = single pulse
T_s = 80 °C
V_{GE} = 15 V
T_j = T_{jmax}

figure 14. **IGBT**

Gate voltage vs gate charge

V_{GE} = f(Q_g)



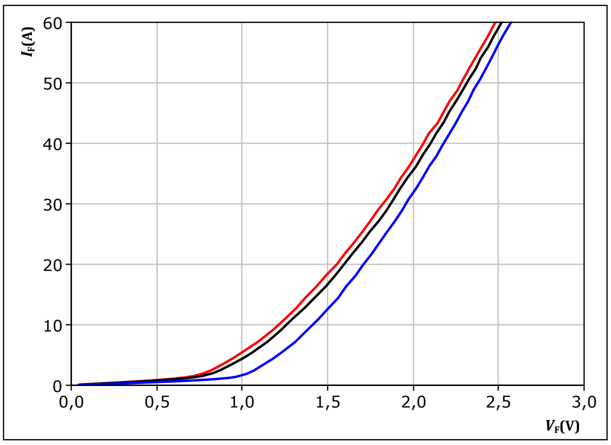
I_C = 50 A
T_j = 25 °C

Brake Diode Characteristics

figure 15. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



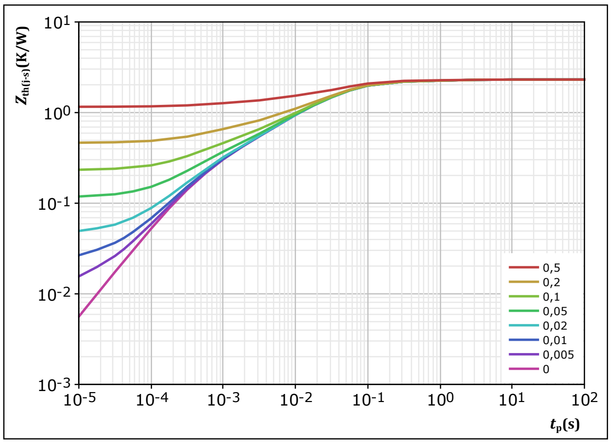
t_p = 250 μs

T_j: 25 °C, 125 °C, 150 °C

figure 16. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 2,315 K/W

FWD thermal model values

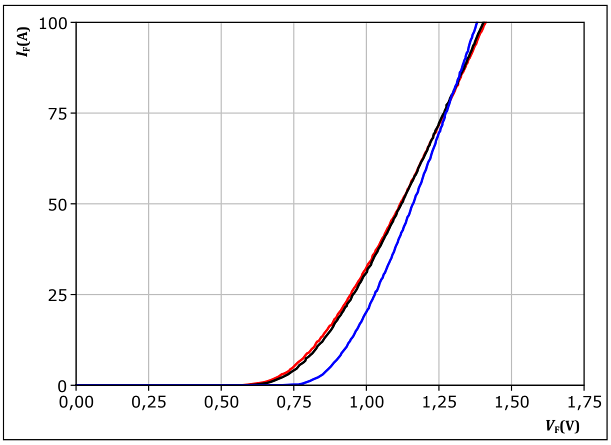
R (K/W)	τ (s)
1,13E-01	1,64E+00
4,74E-01	1,08E-01
1,12E+00	2,89E-02
4,12E-01	4,03E-03
1,94E-01	4,61E-04

Rectifier Diode Characteristics

figure 17. **Rectifier**

Typical forward characteristics

$I_F = f(V_F)$



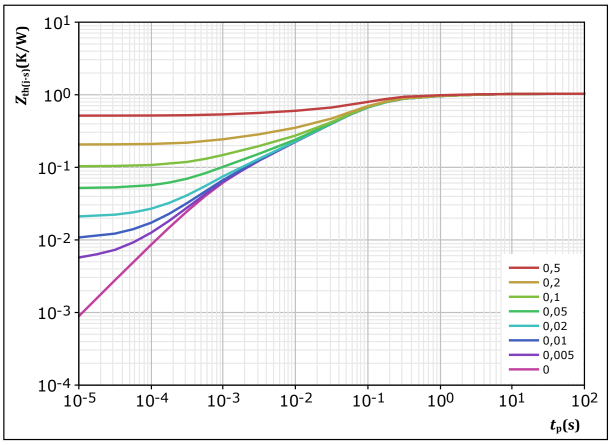
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 18. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 1,032 K/W

Rectifier thermal model values

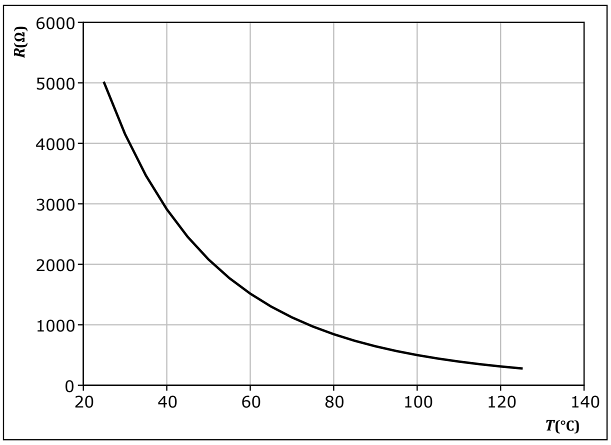
R (K/W)	τ (s)
4,86E-02	5,67E+00
1,31E-01	6,68E-01
5,24E-01	9,95E-02
1,97E-01	3,35E-02
8,14E-02	4,54E-03
4,98E-02	8,29E-04

Thermistor Characteristics

figure 19. **Thermistor**

Typical NTC characteristic as function of temperature

R_T = f(T)

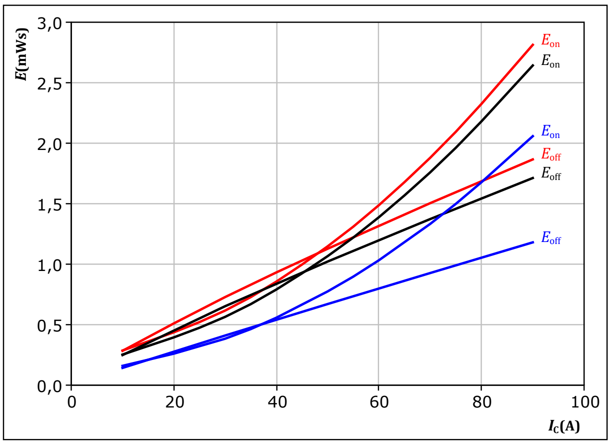


Inverter Switching Characteristics

figure 20. IGBT

Typical switching energy losses as a function of collector current

E = f(I_C)



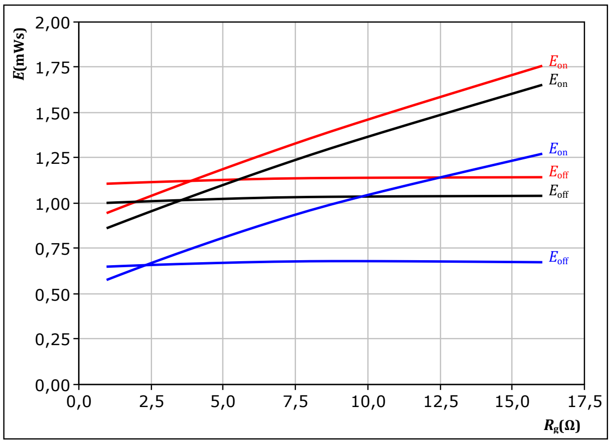
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C
R_{goff} =	4	Ω		

figure 21. IGBT

Typical switching energy losses as a function of IGBT turn on gate resistor

E = f(R_g)



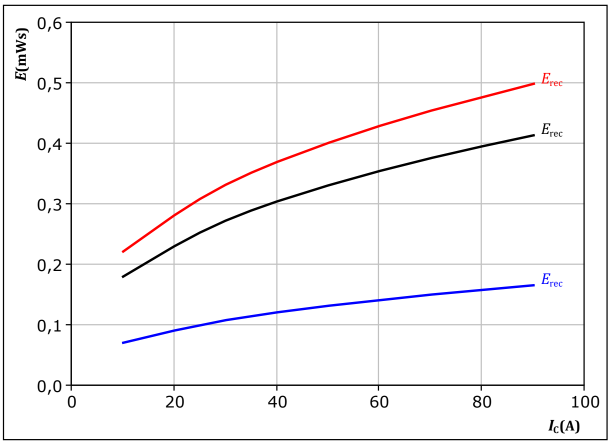
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	50	A		150 °C

figure 22. FWD

Typical reverse recovered energy loss as a function of collector current

E_{rec} = f(I_C)



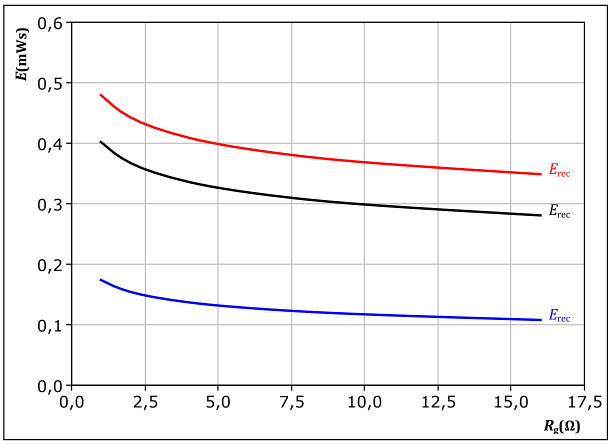
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 23. FWD

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

E_{rec} = f(R_g)



With an inductive load at

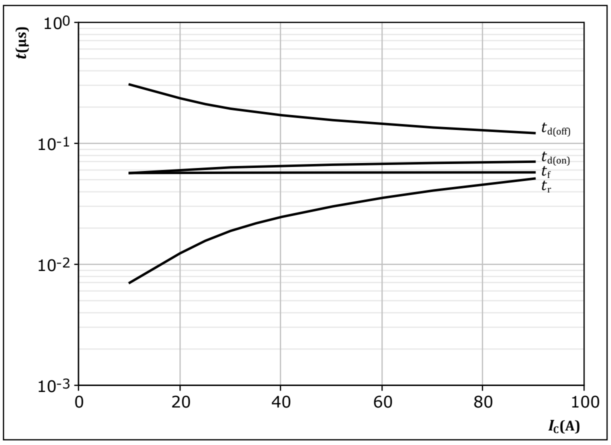
V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	50	A		150 °C

Inverter Switching Characteristics

figure 24. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



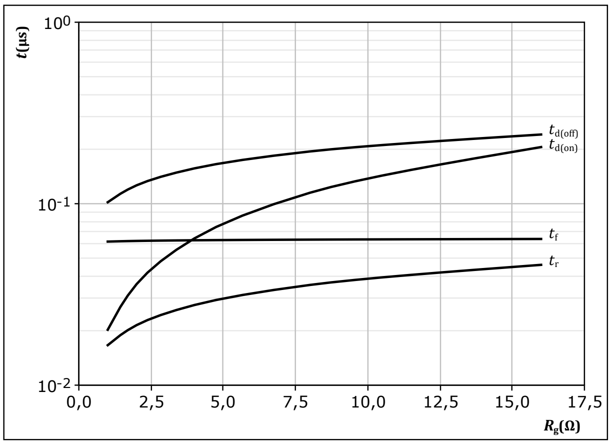
With an inductive load at

T_j =	150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 25. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

$t = f(R_g)$



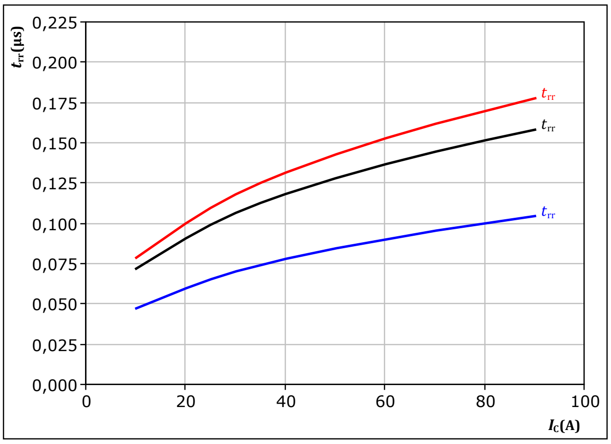
With an inductive load at

T_j =	150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
I_C =	50	A

figure 26. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



With an inductive load at

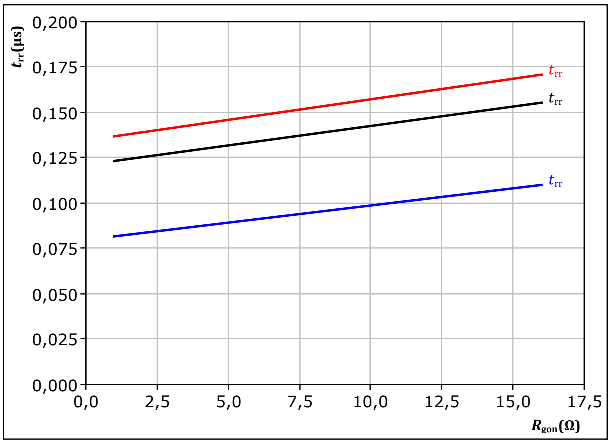
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	4	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 27. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



With an inductive load at

V_{CE} =	300	V
V_{GE} =	±15	V
I_C =	50	A

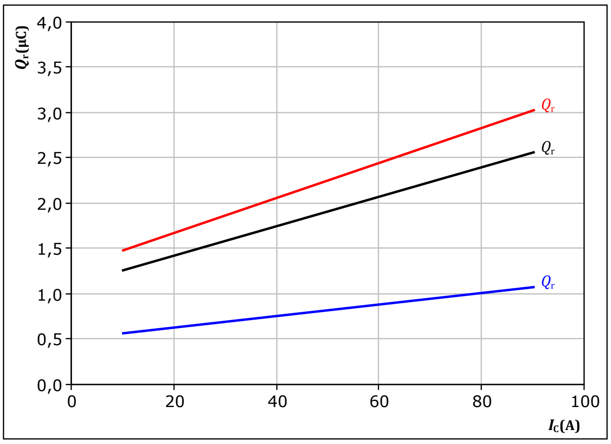
T_j: 25 °C, 125 °C, 150 °C

Inverter Switching Characteristics

figure 28. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



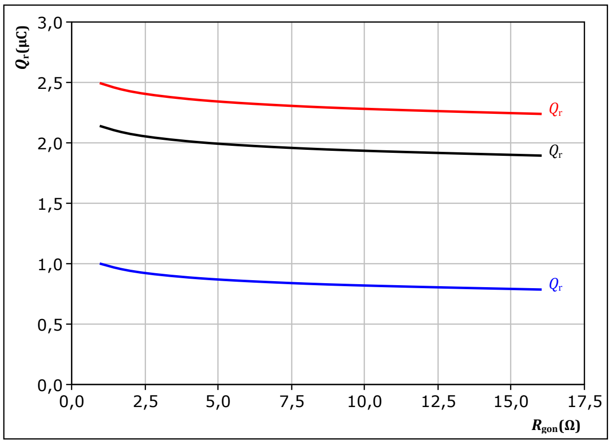
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 29. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



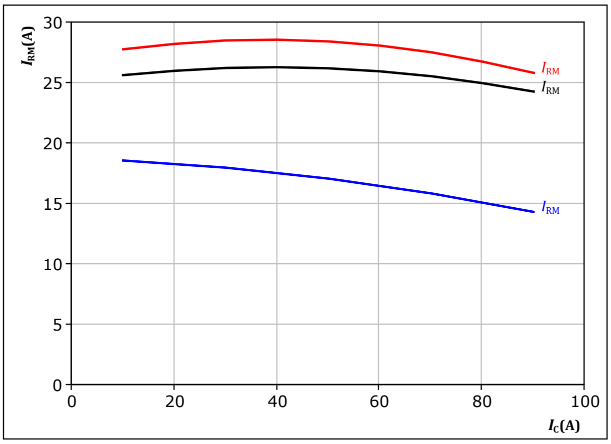
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	50	A		150 °C

figure 30. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



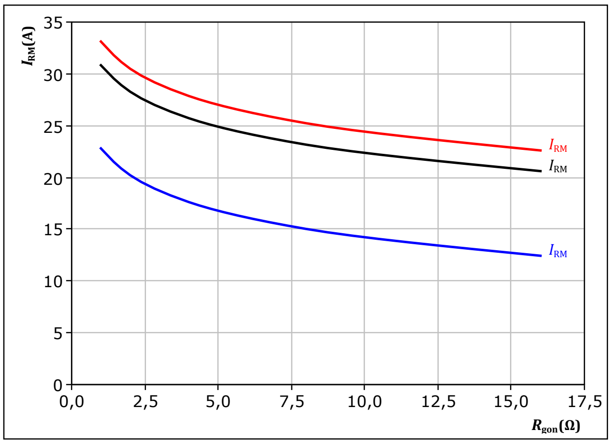
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 31. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

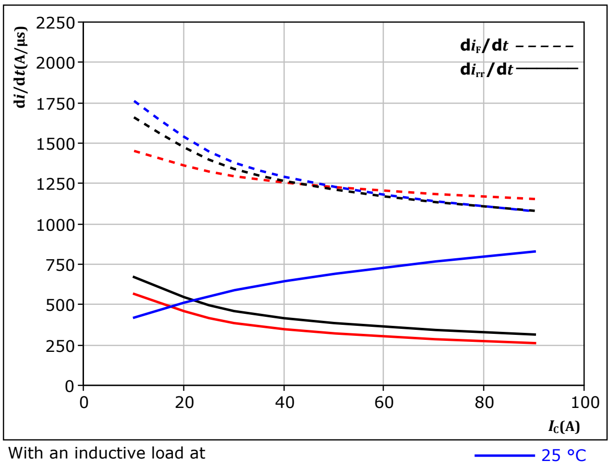
V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	50	A		150 °C

Inverter Switching Characteristics

figure 32. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

di_F/dt, di_{rr}/dt = f(I_C)



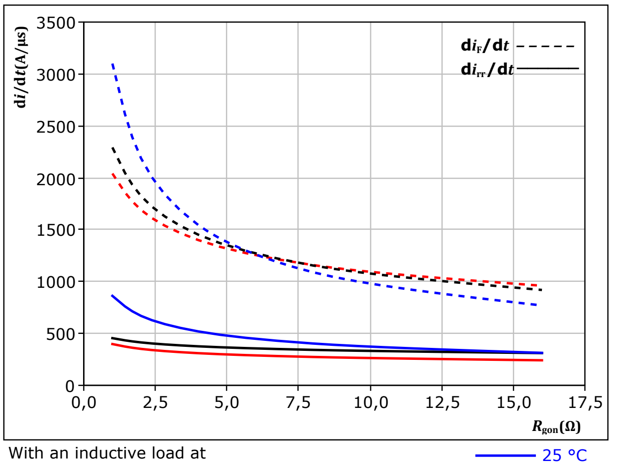
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 33. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})



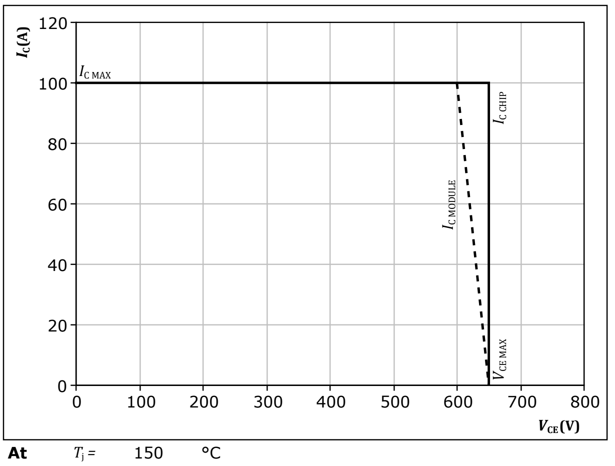
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C
V_{GE} =	±15	V		125 °C
I_C =	50	A		150 °C

figure 34. **IGBT**

Reverse bias safe operating area

I_C = f(V_{CE})



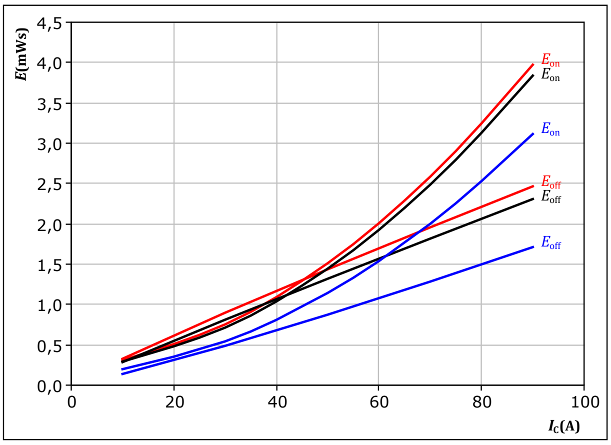
At	T_j =	150	°C
	R_{gon} =	4	Ω
	R_{goff} =	4	Ω

Brake Switching Characteristics

figure 35. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



With an inductive load at

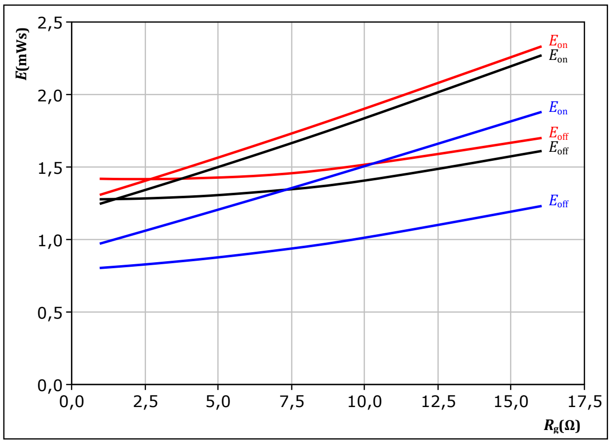
T_j: 25 °C, 125 °C, 150 °C

V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 36. **IGBT**

Typical switching energy losses as a function of IGBT turn on gate resistor

$E = f(R_g)$



With an inductive load at

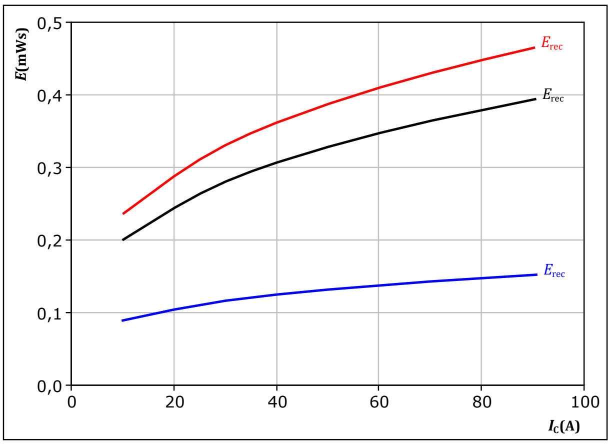
T_j: 25 °C, 125 °C, 150 °C

V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	50	A

figure 37. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



With an inductive load at

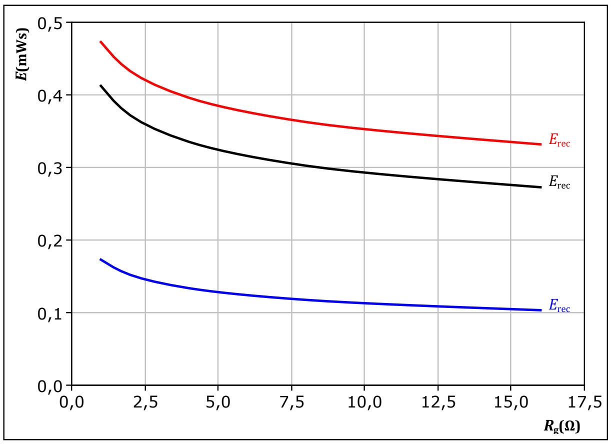
T_j: 25 °C, 125 °C, 150 °C

V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	4	Ω

figure 38. **FWD**

Typical reverse recovered energy loss as a function of IGBT turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

T_j: 25 °C, 125 °C, 150 °C

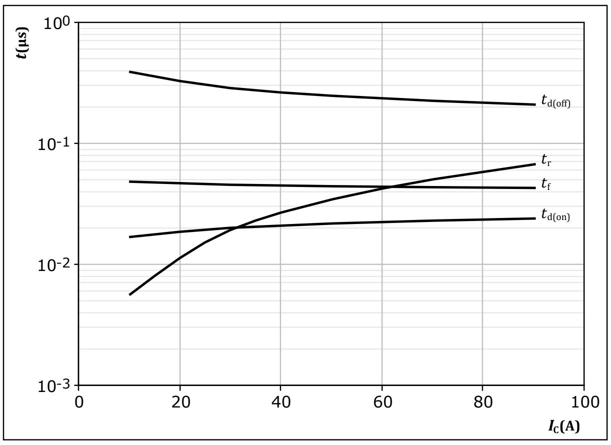
V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	50	A

Brake Switching Characteristics

figure 39. **IGBT**

Typical switching times as a function of collector current

t = f(I_C)



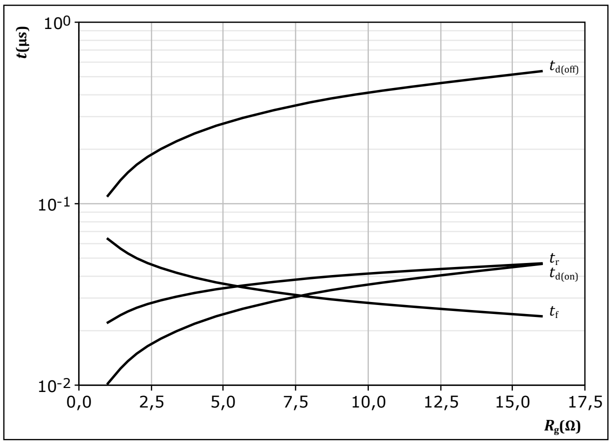
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 40. **IGBT**

Typical switching times as a function of IGBT turn on gate resistor

t = f(R_g)



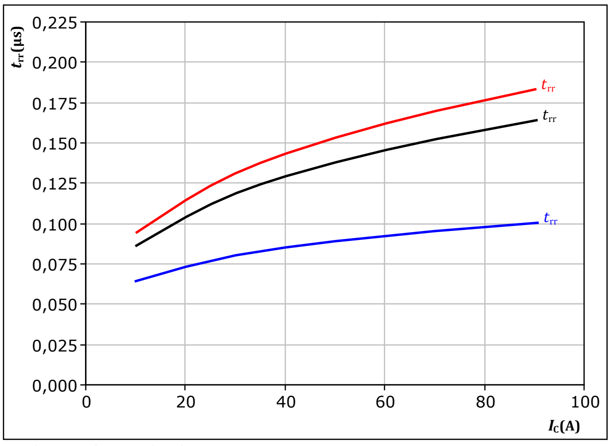
With an inductive load at

T_j =	150	°C
V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	50	A

figure 41. **FWD**

Typical reverse recovery time as a function of collector current

t_{rr} = f(I_C)



With an inductive load at

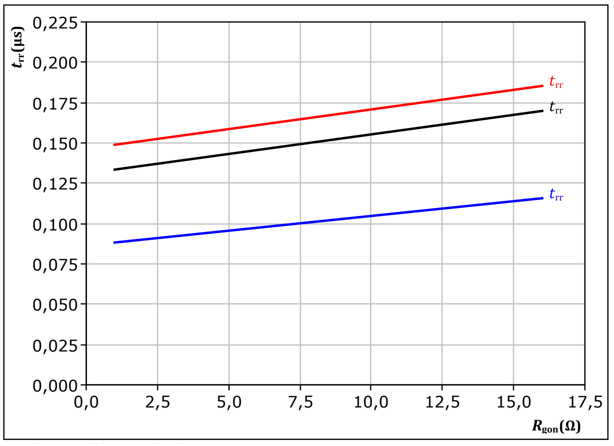
V_{CE} =	400	V
V_{GE} =	0/15	V
R_{gon} =	4	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 42. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

t_{rr} = f(R_{gon})



With an inductive load at

V_{CE} =	400	V
V_{GE} =	0/15	V
I_C =	50	A

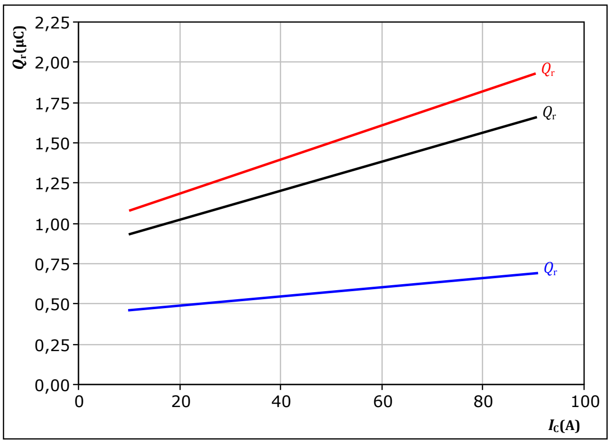
T_j: 25 °C, 125 °C, 150 °C

Brake Switching Characteristics

figure 43. **FWD**

Typical recovered charge as a function of collector current

Q_r = f(I_C)



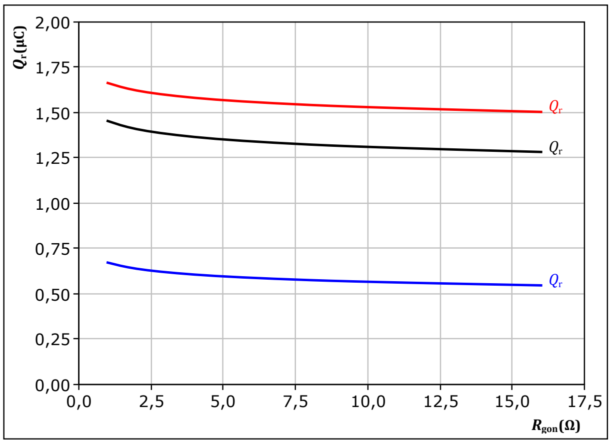
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 44. **FWD**

Typical recovered charge as a function of IGBT turn on gate resistor

Q_r = f(R_{gon})



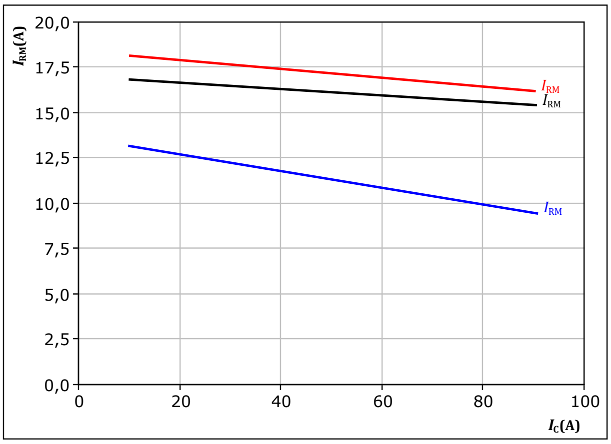
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	50	A		150 °C

figure 45. **FWD**

Typical peak reverse recovery current as a function of collector current

I_{RM} = f(I_C)



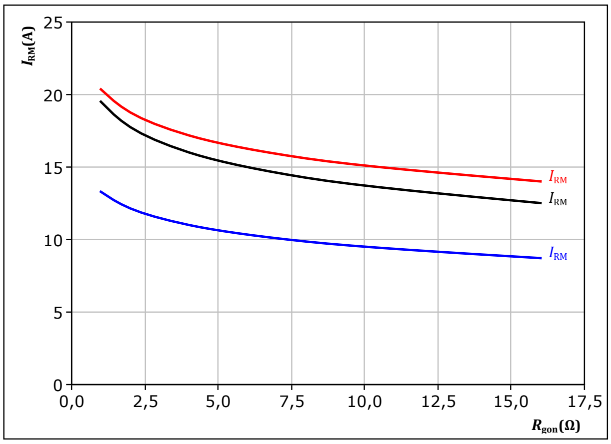
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 46. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

I_{RM} = f(R_{gon})



With an inductive load at

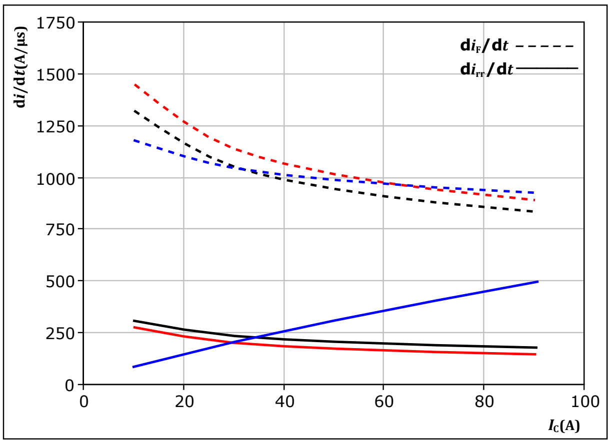
V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	50	A		150 °C

Brake Switching Characteristics

figure 47. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$di_F/dt, di_{rr}/dt = f(I_C)$



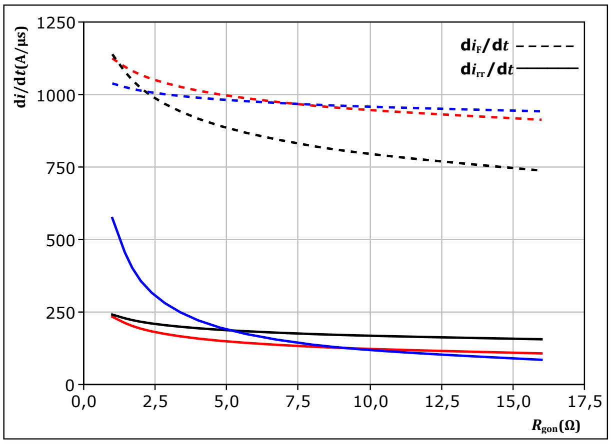
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
R_{gon} =	4	Ω		150 °C

figure 48. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

$di_F/dt, di_{rr}/dt = f(R_{gon})$



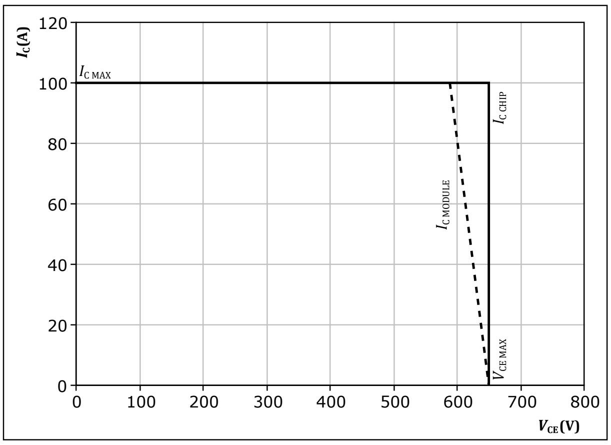
With an inductive load at

V_{CE} =	400	V	T_j:	25 °C
V_{GE} =	0/15	V		125 °C
I_C =	50	A		150 °C

figure 49. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At	T_j =	150	°C
	R_{gon} =	4	Ω
	R_{goff} =	4	Ω

Switching Definitions

figure 50. **IGBT**

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{tEoff} = **integrating time for** E_{off})

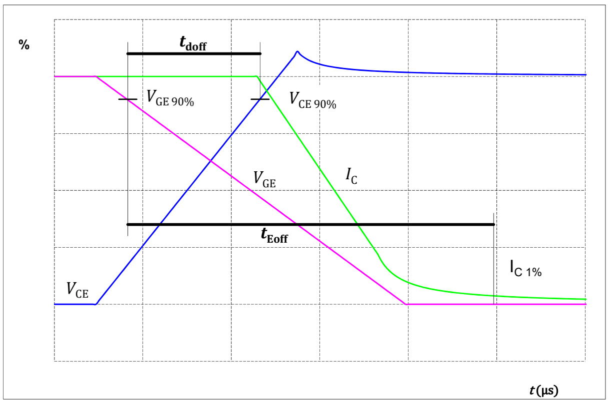


figure 51. **IGBT**

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = **integrating time for** E_{on})

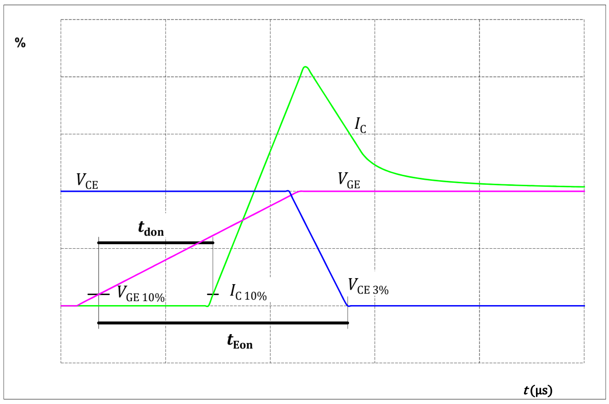


figure 52. **IGBT**

Turn-off Switching Waveforms & definition of t_f

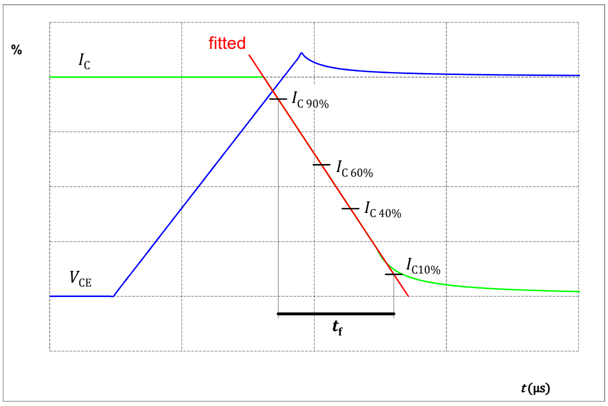
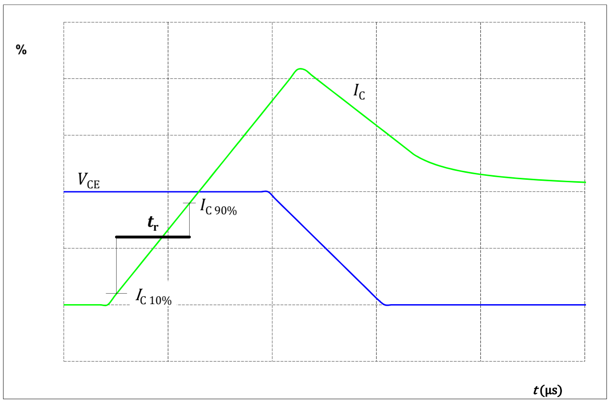


figure 53. **IGBT**

Turn-on Switching Waveforms & definition of t_r



Switching Definitions

figure 54. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

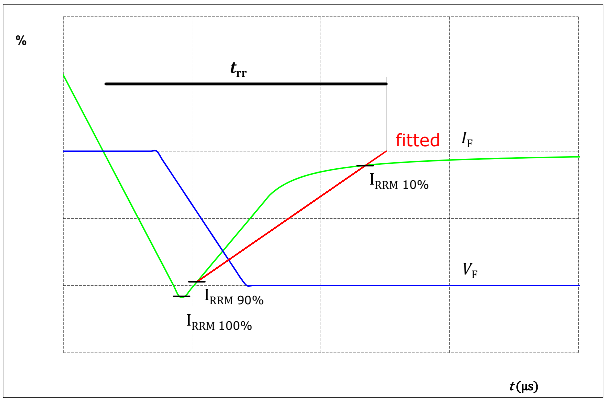
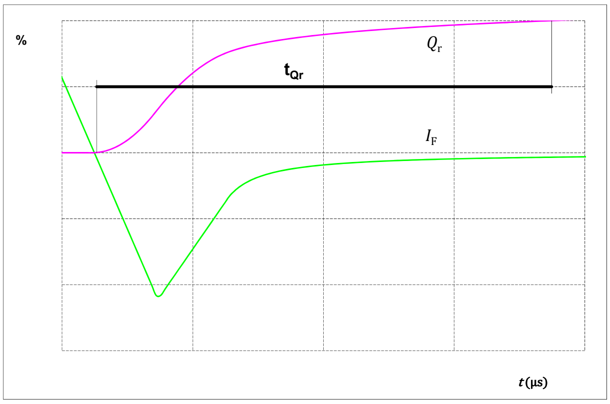


figure 55. **FWD**

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



10-EY07PMA050I7-L184A28T
datasheet

Ordering Code

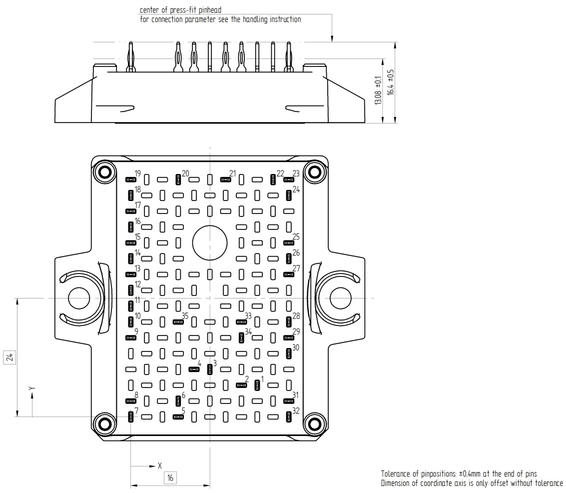
Version	Ordering Code
Without thermal paste	10-EY07PMA050I7-L184A28T
With thermal paste (5,2 W/mK, PTM6000HV)	10-EY07PMA050I7-L184A28T-/7/

Marking

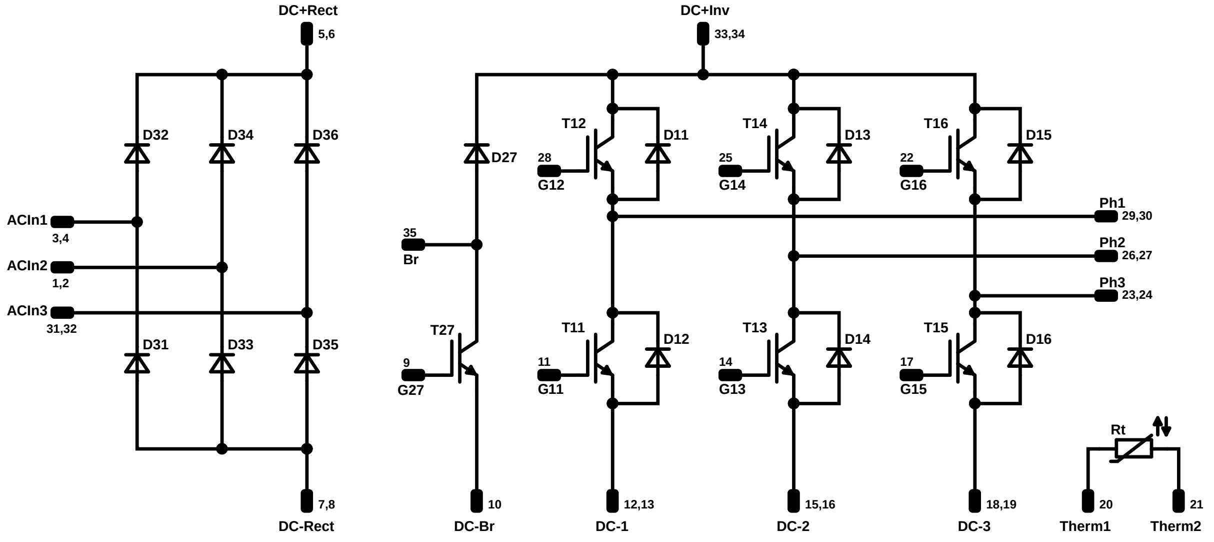
	Text	Name		Date code	UL & VIN	Lot	Serial
		NN-NNNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Datamatrix	Type&Ver	Lot number	Serial	Date code		
		TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

Pin table [mm]			
Pin	X	Y	Function
1	25,6	6,4	ACIn2
2	22,4	6,4	ACIn2
3	16	9,6	ACIn1
4	12,8	9,6	ACIn1
5	9,6	0	DC+Rect
6	9,6	3,2	DC+Rect
7	0	0	DC-Rect
8	0	3,2	DC-Rect
9	0	16	G27
10	0	19,2	DC-Br
11	0	22,4	G11
12	0	25,6	DC-1
13	0	28,8	DC-1
14	0	32	G13
15	0	35,2	DC-2
16	0	38,4	DC-2
17	0	41,6	G15
18	0	44,8	DC-3
19	0	48	DC-3
20	9,6	48	Therm1
21	19,2	48	Therm2
22	28,8	48	G16
23	32	48	Ph3
24	32	44,8	Ph3
25	32	35,2	G14
26	32	32	Ph2
27	32	28,8	Ph2
28	32	19,2	G12
29	32	16	Ph1
30	32	12,8	Ph1
31	32	3,2	ACIn3
32	32	0	ACIn3
33	22,4	19,2	DC+Inv
34	22,4	16	DC+Inv
35	9,6	19,2	Br



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T12, T13, T14, T15, T16	IGBT	650 V	50 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	650 V	50 A	Inverter Diode	
T27	IGBT	650 V	50 A	Brake Switch	
D27	FWD	650 V	20 A	Brake Diode	
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	35 A	Rectifier Diode	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* E2 packages see vincotech.com website.

Package data
Package data for *flow* E2 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}$=175°C and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-EY07PMA050I7-L184A28T-D1-14	2 Jul. 2025	Initial Release	